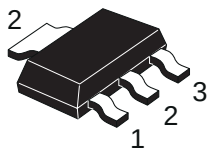
STN888

HIGH CURRENT, HIGH PERFORMANCE, LOW VOLTAGE PNP TRANSISTOR

Ordering Code	Marking
STN888	N888

- VERY LOW COLLECTOR TO EMITTER SATURATION VOLTAGE
- D.C CURRENT GAIN, h_{FE} > 100
- 5 A CONTINUOUS COLLECTOR CURRENT
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- AVAILABLE IN TAPE AND REEL PACKING



SOT-223

APPLICATIONS

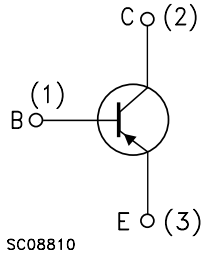
- POWER MANAGEMENT IN PORTABLE EQUIPMENT
- VOLTAGE REGULATION IN BIAS SUPPLY CIRCUITS
- SWITCHING REGULATOR IN BATTERY CHARGER APPLICATIONS
- HEAVY LOAD DRIVER

DESCRIPTION

The device is manufactured in low voltage PNP Planar Technology by using a "Base Island" layout.

The resulting Transistor shows exceptional high gain performance coupled with very low saturation voltage.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I_E = 0)	-60	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	-30	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	-6	V
I_C	Collector Current	-5	A
I_{CM}	Collector Peak Current (t_p < 5 ms)	-10	A
P_{tot}	Total Dissipation at T_{amb} = 25 °C	1.6	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

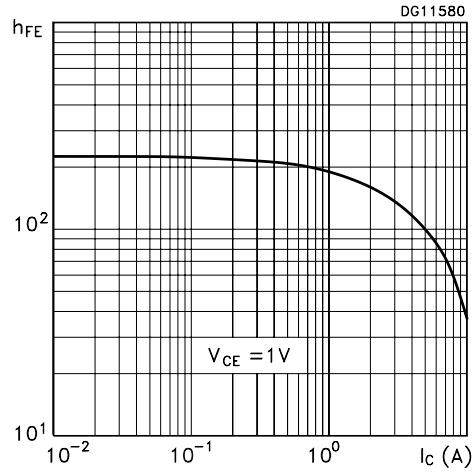
$R_{thj\text{-}amb}$ •	Thermal Resistance Junction-Ambient	Max	78	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

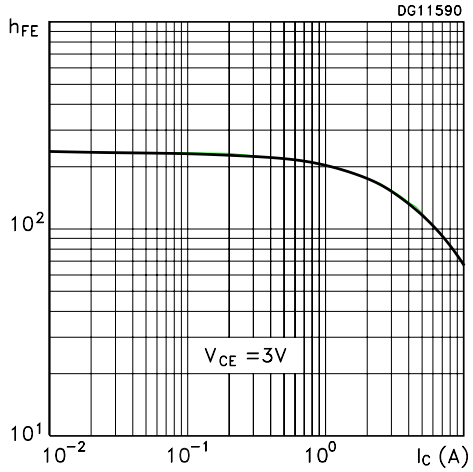
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current (I_E = 0)	V_{CB} = -30 V V_{CB} = -30 V T_j = 100 °C			-10 -1	nA µA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = -6 V			-10	nA
$V_{(BR)CEO}$*	Collector-Emitter Breakdown Voltage (I_B = 0)	I_C = -10 mA	-30			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (I_E = 0)	I_C = -100 µA	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I_C = 0)	I_E = -100 µA	-6			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = -500 mA I_B = -5 mA I_C = -2 A I_B = -50 mA I_C = -5 A I_B = -250 mA I_C = -6 A I_B = -250 mA I_C = -8 A I_B = -400 mA I_C = -10 A I_B = -500 mA			-0.15 -0.25 -0.70 -0.70 -1 -1.5	V V V V V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = -2 A I_B = -50 mA I_C = -6 A I_B = -250 mA			-1.1 -1.4	V V
h_{FE}*	DC Current Gain	I_C = -10 mA V_{CE} = -1 V I_C = -500 mA V_{CE} = -1 V I_C = -5 A V_{CE} = -1 V I_C = -5 A V_{CE} = -1V T_j = 100°C I_C = -8 A V_{CE} = -1 V I_C = -10 A V_{CE} = -1 V	150 150 75 75 40 15	200 200 100 100 55 35	 300 	
 t_d t_r t_s t_f	RESISTIVE LOAD Delay Time RiseTime StorageTime Fall Time	I_C = -3 A I_{B1} = - I_{B2} = -60 mA V_{CC} = -20 V (see figure 1)		 180 160 250 80	 220 210 300 100	 ns ns ns ns

∗ Pulsed: Pulse duration = 300 µs, duty cycle ≤ 1.5 %

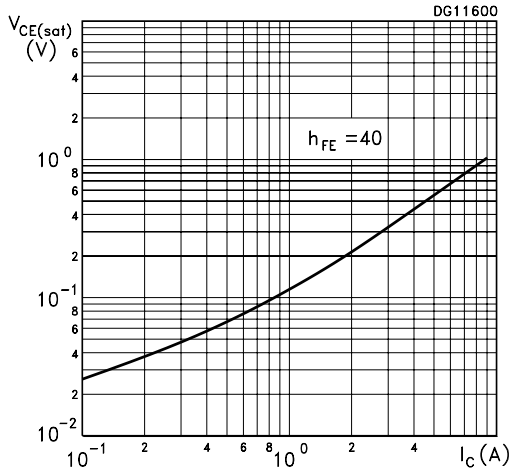
DC Current Gain



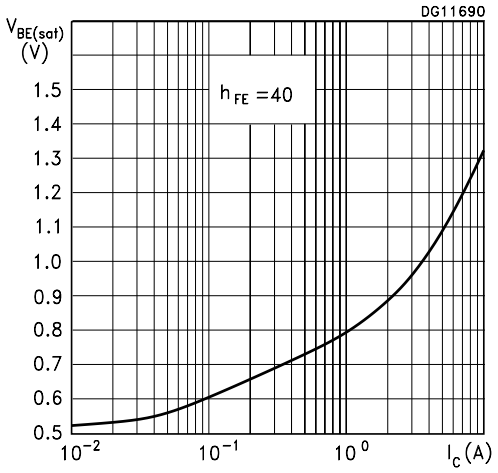
DC Current Gain



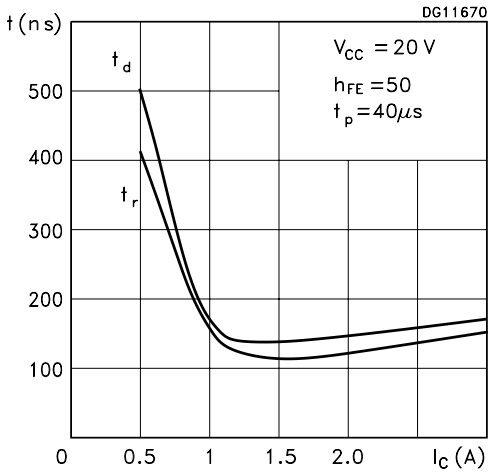
Collector-Emitter Saturation Voltage



Base-Emitter Saturation Voltage



Switching Times Resistive Load



Switching Times Resistive Load

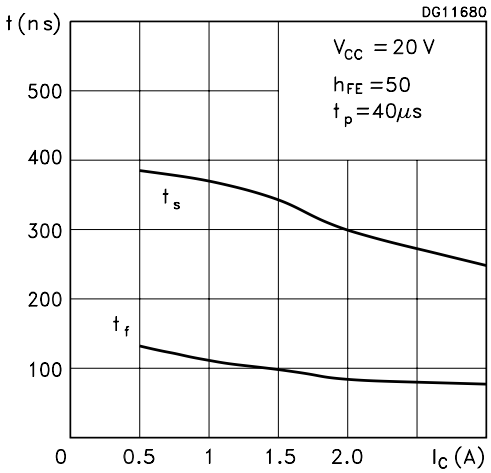
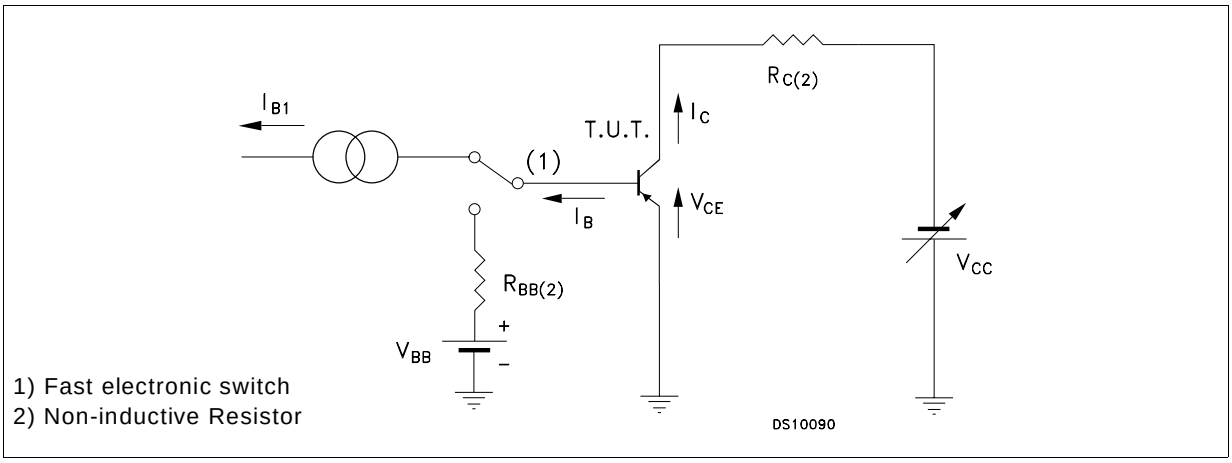


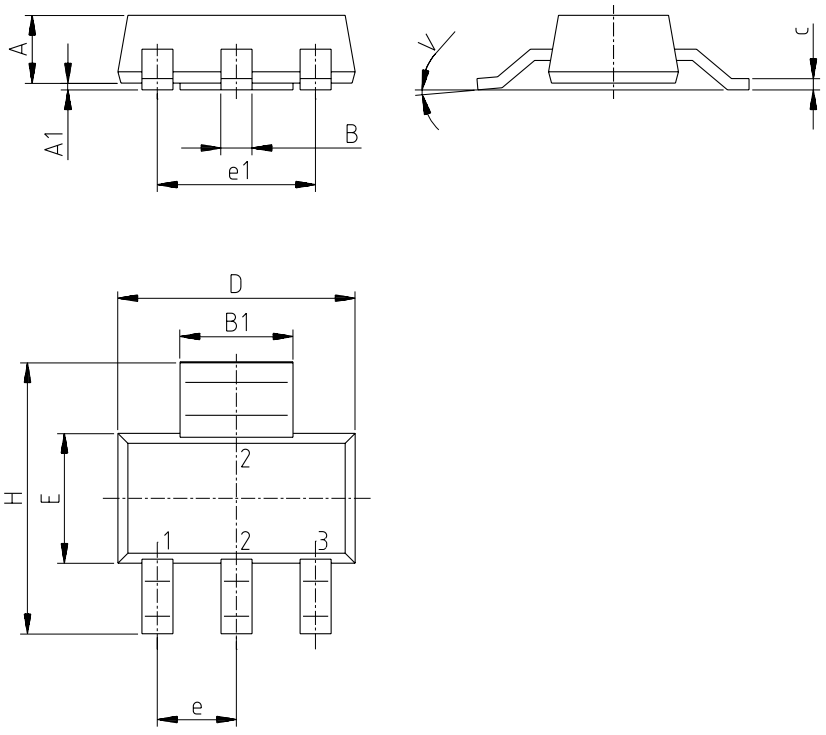
Figure 1: Resistive Load Switching Test Circuits.



1) Fast electronic switch
2) Non-inductive Resistor

SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10^o			10^o
A1		0.02				



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